

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	60358	(high near5 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:09
L2	5408	L1 and passivat\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 18:07
L3	4542	L2 and etch\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 16:15
L4	3104	L3 and plasma	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 16:15
L5	263	L4 and ((treat\$3 passivat\$3) near10 (dielectric insulat\$3) near10 etch\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:59
L6	0	(treat\$3 passivat\$3) near10 oxide near10 etch43	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 16:21
L7	2657	((treat\$3 passivat\$3) near10 (dielectric insulat\$3) near10 etch\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 16:22
L8	246	7 and (high near5 dielectric near5 ("k" constant))	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 16:33
L12	6525	amorph\$5 same (dielectric oxide) same etch\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:14
L13	4577	12 and gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:14
L14	1647	13 and (gate near5 (dielectric inulat\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:15
L15	1389	14 and (ion plasma)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:16
L16	320	15 and (high near5 dielectric near5 ("k" constant))	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 16:34

L17	29060	(high near5 dielectric)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/18 18:03
L19	188	L17 and passivat\$3	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/18 17:10
L20	1309	amorph\$5 same (dielectric oxide) same etch\$3	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/18 17:14
L22	494	20 and gate	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/18 17:14
L23	3584	13 and (gate near5 (dielectric insulat\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 18:02
L24	3091	23 and (ion plasma)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:16
L25	111	L24 and ((treat\$3 passivat\$3).near10 (dielectric insulat\$3) near10 etch\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 17:59
L26	229	22 and (gate near5 (dielectric insulat\$3))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/18 18:02
L27	4	26 and (high same dielectric same (constant "K"))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/18 18:03
L28	1	"20050064716"	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/18 18:07